

Burr-Brown Products from Texas Instruments





SBAS150A - AUGUST 1987 - REVISED FEBRUARY 2003

CMOS 12-Bit Multiplying DIGITAL-TO-ANALOG CONVERTER Microprocessor Compatible

FEATURES

- FOUR-QUADRANT MULTIPLICATION
- LOW-GAIN TC: 2ppm/°C typ
- MONOTONICITY ENSURED OVER TEMPERATURE
- SINGLE 5V TO 15V SUPPLY
- TTL/CMOS LOGIC COMPATIBLE
- LOW OUTPUT LEAKAGE: 10nA max
- LOW OUTPUT CAPACITANCE: 70pF max
- DIRECT REPLACEMENT FOR THE AD7545, PM-7545

DESCRIPTION

The DAC7545 is a low-cost, CMOS, 12-bit, four-quadrant multiplying, digital-to-analog converter (DAC) with input data latches. The input data is loaded into the DAC as a 12-bit data word. The data flows through to the DAC when both the chip select (\overline{CS}) and the write (\overline{WR}) pins are at a logic low.

Laser-trimmed thin-film resistors and excellent CMOS voltage switches provide true 12-bit integral and differential linearity. The device operates on a single +5V to +15V supply and is available in an SO-20 package; devices are specified over the commercial temperature range.

The DAC7545 is well suited for battery-powered or other lowpower applications because the power dissipation is less than 0.5mW when used with CMOS logic inputs and $V_{DD} = +5V$.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

 $T_A = +25^{\circ}C$, unless otherwise noted.

NO COND	0.01/ 17
V _{DD} to DGND	–0.3V, +17
Digital Input to DGND	–0.3V, V _{DD}
V _{RFB} , V _{REF} , to DGND	±25V
V _{PIN 1} to DGND	–0.3V, V _{DD}
AGND to DGND	–0.3V, V _{DD}
Power Dissipation: Any Package to +75°C	
Derates above +75°C by	6mW/°C
Operating Temperature:	
Commercial J, K, L, and GL	40°C to +85°C
Storage Temperature	–65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

NOTE: (1) Stresses above those listed above may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

PACKAGE/ORDERING INFORMATION

PRODUCT	RELATIVE ACCURACY (LSB)	GAIN ERROR (LSB) V _{DD} = +5V	PACKAGE-LEAD	PACKAGE DESIGNATOR ⁽¹⁾	SPECIFIED TEMPERATURE RANGE	PACKAGE MARKING	ORDERING NUMBER	TRANSPORT MEDIA, QUANTITY
DAC7545	±2	±20	SO-20	DW	-40°C to +85°C	DAC7545JU	DAC7545JU	Rails, 38
"	±1	±10	"	"	"	DAC7545KU	DAC7545KU	Rails, 38
DAC7545	±1/2	±5	SO-20	DW	-40°C to +85°C	DAC7545LU	DAC7545LU	Rails, 38
"	±1/2	±2	"	"	"	DAC7545GLU	DAC7545GLU	Rails, 38

NOTE: (1) For the most current specifications and package information, refer to our web site at www.ti.com.

PIN CONNECTIONS



WRITE CYCLE TIMING DIAGRAM







ELECTRICAL CHARACTERISTICS

 V_{REF} = +10V, $V_{OUT 1}$ = 0V, and ACOM = DCOM, unless otherwise specified.

$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$				DAC	7545			
PARMETER GRADE $T_{a} = +25^{cc}$ $T_{axx} T_{axt}$ ⁽¹⁾ UNITS TEST CONDITIONS/COMMENTS STATUC PERFORMANCE Resolution Accuracy All 12			V _{DD} :	= +5V	V _{DD} = +15V			
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	PARAMETER	GRADE	T _A = +25°C	T _{MAX} -T _{MIN} ⁽¹⁾	T _A = +25°C	T _{MAX} -T _{MIN} ⁽¹⁾	UNITS	TEST CONDITIONS/COMMENTS
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	STATIC PERFORMANCE							
$ \begin{array}{cccc} Accuracy & J & J & J & J & J & J & J & J & J & $	Resolution	All	12	12	12	12	Bits	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Accuracy	J	±2	±2	±2	±2	LSB	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		K	±1	±1	±1	±1	LSB	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		L	±1/2	±1/2	±1/2	±1/2	LSB	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		GL	±1/2	±1/2	±1/2	±1/2	LSB	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Differential Nonlinearity	J	±4	±4	±4	±4	LSB	10-Bit Monotonic, T _{MIN} to T _{MAX}
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		К	±1	±1	±1	±1	LSB	10-Bit Monotonic, T _{MIN} to T _{MAX}
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		L	±1	±1	±1	±1	LSB	12-Bit Monotonic, T _{MIN} to T _{MAX}
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		GL	±1	±1	±1	±1	LSB	12-Bit Monotonic, T _{MIN} to T _{MAX}
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Gain Error (with internal R _{FB}) ⁽²⁾	J	±20	±20	±25	±25	LSB	DAC register loaded with FFF _H .
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		К	±10	±10	±15	±15	LSB	Gain error is adjustable using
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		L	±5	±6	±10	±10	LSB	the circuits in Figures 2 and 3.
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		GL	±2	±3	±6	±7	LSB	l
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gain Temperature Coefficient ⁽³⁾							
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	(∆Gain/∆Temperature)	All	±5	±5	±10	±10 fr	ppm/°C or V _{DD} = +	Typical Value is 2ppm/°C
$\begin{array}{c cl} (A3 an AV_{DD}) & Ail & 0.015 & 0.03 & 0.01 & 50 & nA & DB_{2}DB_{11} = 0V; \overline{WR}, \overline{CS} = 0V \\ \hline DYNAMC PERFORMANCE \\ Current Settling Time!(3) & Ail & 2 & 2 & 2 & 2 & \mus & To 1/2 LSB. Out 1 Load = 1000. DC2 of WR, \overline{CS} = 0V \\ \hline DYNAMC PERFORMANCE \\ Current Settling Time!(3) & Ail & 2 & 2 & 2 & 2 & \mus & To 1/2 LSB. Out 1 Load = 1000. DC2 of WR, \overline{CS} = 0V \\ \hline Propagation Delay(3) (from digital input change to 90% of final analog output) & Ail & 300 & 250 & nV & VPD & VREF = 13pF(4) \\ Other Change to 90% of final analog output) & Ail & 400 & 250 & nV & VPD & VREF = 120V, 10 kHz Sine Wave \\ \hline REFFERENCE INPUT \\ Input Resistance (pin 19 to AGND) & Ail & 7 & 7 & 7 & 7 & kQ(0) \\ Output Capacitance(3): Court & Ail & 70 & 70 & 70 & 70 & pF & DB_0 DB_{11} = 0V; \overline{WR}, \overline{CS} = 0V \\ \hline DIGITAL INPUTS \\ Output Capacitance(3): Court & Ail & 200 & 200 & 200 & pF & DB_0 DB_{11} = 0V; \overline{WR}, \overline{CS} = 0V \\ \hline DIGITAL INPUTS & Ail & 20 & 200 & 200 & pF & DB_0 DB_{11} = VD; \overline{WR}, \overline{CS} = 0V \\ \hline M_{10} (Input HOH Voltage) & Ail & 24 & 24 & 13.5 & 13.5 & VV \\ M_{10} (Input LOW Voltage) & Ail & 24 & 22 & 20 & 20 & 20 & pF \\ \hline V_{10} (Input Current)^{(1)} & Ail & 21 & \pm 10 & \pm 1 & \pm 10 & \pm 1 & \pm 10 & \mu A \\ \hline M_{10} (Input LOW Voltage) & Ail & 22 & 22 & 20 & 20 & pF & V_{M} = 0V or V_{DD} \\ \hline DIGITAL INPUTS & Ail & 220 & 220 & 20 & 20 & pF & V_{M} = 0V & V_{DD} \\ \hline M_{11} (Digu LOW Voltage) & Ail & 260 & 380 & 180 & 200 & ns^{(6)} \\ \hline Chip Select to Write Setup Time, t_{CS} & Ail & 200 & 270 & 120 & ns^{(6)} \\ Data Setup Time, t_{DS} & Ail & 140 & 10 & 10 & ns^{(6)} \\ \hline Data Setup Time, t_{DS} & Ail & 100 & 100 & 100 & 100 & ns^{(6)} \\ \hline Data Hold Time, t_{DH} & Ail & 10 & 10 & 10 & ns^{(6)} \\ \hline POWER SUPPLY, t_{DD} & Ail & 2 & 2 & 2 & 2 & 2 & mA \\ \hline Ail & 100 & 10 & 10 & 10 & 10 & 10 & 10 \\ \hline Data Hold Time, t_{DH} & Ail & 10 & 10 & 10 & 10 \\ \hline Data Hold Time, t_{DH} & Ail & 10 & 10 & 10 & 10 & 10 \\ \hline Data Hold Time, t_{DH} & Ail & 10 & 10 & 10 & 10 & 10 \\ \hline Data Hold Time, t_{DH} & Ail & 10 & 10 & 10 & 10 \\ $	DC Supply Rejection ⁽³⁾							
Output Leakage Current at Out 1 J, K, L, GL 10 50 10 10 100 10 10 10 10 10 50 10 50 10 10 100 100 100 10 10 10 100	(ΔGain/ΔV _{DD})	All	0.015	0.03	0.01	0.02	%/%	$\Delta V_{DD} \pm 5\%$
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Output Leakage Current at Out 1	J, K, L, GL	10	50	10	50	nA	$DB_0 - DB_{11} = 0V; WR, CS = 0V$
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	DYNAMIC PERFORMANCE							
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Current Settling Time ⁽³⁾	All	2	2	2	2	μs	To 1/2 LSB. Out 1 Load = 100Ω
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	_							DAC output measured from
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $								falling edge of \overline{WR} . $\overline{CS} = 0V$.
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Bropagation Dolov(3) (from digital input	A.II						
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	change to 00% of final analog output)	All	200		250		-	Out 1 l and -1000 C $-12 n E^{(4)}$
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		A.II	300		250		n\/ o(5)	Out I Load = 10022 . $C_{EXT} = 13pF(.)$
$\begin{array}{c c c c c c c c c c c c c c c c c c c $			400	5	230		m\/n n ⁽⁵⁾	$V_{\text{REF}} = ACOW$
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		All	5	5	5	5	mvp-p(°)	$v_{\text{REF}} = \pm 10^{\circ}$, TOKHZ SITIE Wave
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	REFERENCE INPUT							
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Input Resistance (pin 19 to AGND)	All	7	7	7	7	$k\Omega^{(6)}$	Input Resistance TC = 300ppm/°C ⁽⁵⁾
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			25	25	25	25	kΩ	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	AC OUTPUTS							
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Output Capacitance ⁽³⁾ : COUT 1	All	70	70	70	70	рF	$DB_0 - DB_{11} = 0V$; \overline{WR} , $\overline{CS} = 0V$
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Court 2	All	200	200	200	200	pF	$DB_0 - DB_{11} = V_{DD}; \overline{WR}, \overline{CS} = 0V$
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $							F.	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		A.U.		0.4	40.5	40.5	1/(6)	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{IH} (Input HIGH Voltage)	All	2.4	2.4	13.5	13.5	V(0)	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		All	0.8	0.8	1.5	1.5	V)/ 0)/ or)/
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Input Conseitence ⁽³⁾	All	±1	±10	±1	±10	μΑ	$V_{\rm IN} = 0V \text{ or } V_{\rm DD}$
WR, CS All 20 20 20 20 pr $v_{IN} = 0V$ SWITCHING CHARACTERISTICS ^(a) Chip Select to Write Setup Time, t_{CS} All 280 380 180 200 ns ⁽⁶⁾ See Timing Diagram Chip Select to Write Hold Time, t_{CH} All 0 0 0 ns ⁽⁶⁾ See Timing Diagram Write Pulse Width, t_{WR} All 250 400 160 240 ns ⁽⁶⁾ $t_{CS} \ge t_{WR}, t_{CH} \ge 0$ Data Setup Time, t_{DS} All 140 210 90 120 ns ⁽⁶⁾ $t_{CS} \ge t_{WR}, t_{CH} \ge 0$ Data Hold Time, t_{DH} All 10 10 10 ns ⁽⁶⁾ $t_{CS} \ge t_{WR}, t_{CH} \ge 0$ POWER SUPPLY, I_{DD} All 2 2 2 mA All Digital Inputs V_{IL} or V_{IH} All 100 500 100 500 μA All Digital Inputs $V_{V_{IL}}$ or V_{DD} All 10 10 10 10 4ll Digital Inputs $V_{V_{DD}}$ V_{DD}		All	5	5	5	5	p⊢ 	$V_{\rm IN} = 0V$
$ \begin{array}{ c c c c c c c c } \hline SWITCHING CHARACTERISTICS(*) \\ Chip Select to Write Setup Time, t_{CS} \\ Chip Select to Write Hold Time, t_{CH} \\ Write Pulse Width, t_{WR} \\ \hline Mil \\ Data Setup Time, t_{DS} \\ Data Setup Time, t_{DH} \\ \hline Mil \\ All \\ 10 \\ Data Hold Time, t_{DH} \\ \hline Mil \\ All \\ 10 \\ 10 \\ 10 \\ 10 \\ All \\ 10 \\ 10 \\ 10 \\ 10 \\ 10 \\ 10 \\ 10 \\ $	WR, CS	All	20	20	20	20	рг	V _{IN} = 0V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	SWITCHING CHARACTERISTICS ⁽⁸⁾							
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Chip Select to Write Setup Time, t _{CS}	All	280	380	180	200	ns ⁽⁶⁾	See Timing Diagram
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			200	270	120	150	ns ⁽⁵⁾	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Chip Select to Write Hold Time, t _{CH}	All	0	0	0	0	ns ⁽⁶⁾	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Write Pulse Width, t _{WR}	All	250	400	160	240	ns ⁽⁶⁾	$t_{CS} \ge t_{WR}, t_{CH} \ge 0$
Data Setup Time, t _{DS} All 140 210 90 120 ns ⁽⁶⁾ Data Hold Time, t _{DH} All 100 150 60 80 ns ⁽⁶⁾ POWER SUPPLY, I _{DD} All 10 10 10 10 ns ⁽⁶⁾ All 2 2 2 mA All Digital Inputs V _{IL} or V _{IH} All 100 500 100 500 μA All Digital Inputs V/ or V _{DD} All 10 10 10 10 10 Horizat Inputs V/ or V _{DD}			175	280	100	170	ns ⁽⁵⁾	
Data Hold Time, t _{DH} 100 150 60 80 ns ⁽⁵⁾ POWER SUPPLY, I _{DD} All 10 10 10 10 ns ⁽⁶⁾ All 2 2 2 mA All Digital Inputs V _{IL} or V _{IH} All 100 500 100 500 μA All 10 10 10 10 All Digital Inputs V _{IL} or V _{DD}	Data Setup Time, t _{DS}	All	140	210	90	120	ns ⁽⁶⁾	
Data Hold Time, t _{DH} All 10 10 10 ns ⁽⁶⁾ POWER SUPPLY, I _{DD} All 2 2 2 mA All Digital Inputs V _{IL} or V _{IH} All 100 500 100 500 μA All Digital Inputs V _{IL} or V _{DD} All 100 500 100 10 10 uA			100	150	60	80	ns ⁽⁵⁾	
POWER SUPPLY, I _{DD} All 2 2 2 2 mA All Digital Inputs V _{IL} or V _{IH} All 100 500 100 500 μA All Digital Inputs V _{IL} or V _{DD} All 10 10 10 10 10 UA	Data Hold Time, t _{DH}	All	10	10	10	10	ns ⁽⁶⁾	
All222MAAll Digital Inputs V_{IL} or V_{IH} All100500100500 μA All Digital Inputs 0V or V_{DD} All1010101010 $\mu A^{(5)}$ All Digital Inputs 0V or V_{DD}	POWER SUPPLY, Inc.							
All100500100500 μ AAll Digital Inputs 0V or V_DAll1010101010 μ A		All	2	2	2	2	mA	All Digital Inputs V _{II} or V _{IH}
All 10 10 10 10 UA ⁽⁵⁾ All Digital Inputs OV or V ₂₂		All	100	500	100	500	μA	All Digital Inputs 0V or VDD
		All	10	10	10	10	μA ⁽⁵⁾	All Digital Inputs 0V or VDD

NOTES: (1) Temperature ranges—J, K, L, and GL: -40° C to +85°C. (2) This includes the effect of 5ppm max, gain TC. (3) Ensured but not tested. (4) DB₀-DB₁₁ = 0V to V_{DD} or V_{DD} to 0V. (5) Typical. (6) Minimum. (7) Logic inputs are MOS gates. Typical input current (+25°C) is less than 1nA. (8) Sample tested at +25°C to ensure compliance.



DISCUSSION OF SPECIFICATIONS

RELATIVE ACCURACY

This term (also known as end point linearity) describes the transfer function of analog output to digital input code. Relative accuracy describes the deviation from a straight line after zero and full-scale have been adjusted.

DIFFERENTIAL NONLINEARITY

Differential nonlinearity is the deviation from an ideal 1LSB change in the output, for adjacent input code changes. A differential nonlinearity specification of 1LSB ensures monotonicity.

GAIN ERROR

Gain error is the difference in measure of full-scale output versus the ideal DAC output; the ideal output for the DAC7545 is $-(4095/4096)(V_{REF})$. Gain error can be adjusted to zero using external trims, see the Applications section.

OUTPUT LEAKAGE CURRENT

The current that appears at OUT 1 with the DAC loaded with all zeros.

MULTIPLYING FEEDTHROUGH ERROR

The AC output error due to capacitive feedthrough from V_{REF} to OUT 1 with the DAC loaded with all zeros; this test is performed using a 10kHz sine wave.

OUTPUT CURRENT SETTLING TIME

The time required for the output to settle within ± 0.5 LSB of final value from a change in code of all zeros to all ones, or all ones to all zeros.

PROPAGATION DELAY

The delay of the internal circuitry is measured as the time from a digital code change to the point at which the output reaches 90% of final value.

DIGITAL-TO-ANALOG GLITCH IMPULSE

The area of the glitch energy measured in nanovolt-seconds. Key contributions to glitch energy are internal circuitry timing differences and charge injected from digital logic. The measurement is performed with $V_{REF} = GND$, an OPA600 as the output op amp, and G_1 (phase compensation) = 0pF.

MONOTONICITY

Monotonicity assures that the analog output will increase or stay the same for increasing digital input codes. The DAC7545 is ensured monotonic to 12 bits, except the J grade is specified to be 10-bit monotonic.

POWER-SUPPLY REJECTION

Power-supply rejection is the measure of the sensitivity of the output (full-scale) to a change in the power-supply voltage.

CIRCUIT DESCRIPTION

Figure 1 shows a simplified schematic of the DAC portion of the DAC7545. The current from the V_{REF} pin is switched from OUT 1 to AGND by the FET switch. This circuit architecture keeps the resistance at the reference pin constant and equal to R_{LDR}, so the reference can be provided by either a voltage or current, AC or DC, positive or negative polarity, and have a voltage range up to \pm 20V even with V_{DD} = 5V. The R_{LDR} is equal to R and is typically 11kW.

The output capacitance of the DAC7545 is code dependent and varies from a minimum value (70pF) at code 000h to a maximum (200pF) at code FFFh.

The input buffers are CMOS inverters, designed so that when the DAC7545 is operated from a 5V supply (V_{DD}), the logic threshold is TTL-compatible. Being simple CMOS inverters, there is a range of operation where the inverters operate in the linear region and thus draw more supply current than normal. Minimizing this transition time through the linear region and insuring that the digital inputs are operated as close to the rails as possible will minimize the supply drain current.



FIGURE 1. Simplified DAC Circuit of the DAC7545.



APPLICATIONS

UNIPOLAR OPERATION

Figure 2 shows the DAC7545 connected for unipolar operation. The high-grade DAC7545 is specified for a 1LSB gain error, so gain adjust is typically not needed; however, the resistors shown are for adjusting full-scale errors. The value of R₁ should be minimized to reduce the effects of mismatching temperature coefficients between the internal and external resistors. A range of adjustment of 1.5 times the desired range will be adequate. For example, for a DAC7545JP, the gain error is specified to be ±25LSB, therefore, a range of adjustment of ±37LSB will be adequate. Equation 1 results in a value of 458W for the potentiometer (use 500 Ω).

$$R_{1} = \frac{R_{LADDER}}{4096} \left(3 \bullet \text{Gain Error} \right)$$
(1)



FIGURE 2. Unipolar Binary Operation.

The addition of R_1 will cause a negative gain error. To compensate for this error, R_2 must be added. The value of R_2 should be one-third the value of R_1 .

The capacitor across the feedback resistor is used to compensate for the phase shift due to stray capacitances of the circuit board, the DAC output capacitance, and op amp input capacitance. Eliminating this capacitor will result in excessive ringing and an increase in glitch energy, therefore, this capacitor must be as small as possible to minimize settling time.

The circuit of Figure 2 can be used with input voltages up to $\pm 20V$ as long as the output amplifier is biased to handle the excursions. Table I represents the analog output for four codes into the DAC for Figure 2.

BIPOLAR OPERATION

Figure 3 and Table II illustrate the recommended circuit and code relationship for bipolar operation. The DAC function uses offset binary code. The inverter, U_1 , on the MSB line converts binary two's complement input code to offset binary code. If the inversion is done in software, U_1 can be omitted.

BINARY CODE	ANALOG OUTPUT
MSB LSB 1111 1111 1111 1000 0000 0000 0000 0000 0001	-V _{IN} (4095/4096) -V _{IN} (2048/4096) = −1/2V _{IN} -V _W (1/4096)
0000 0000 0000	0V

TABLE I. Unipolar Codes.

DATA	NPUT	ANALOG OUTPUT					
MSB	LSB						
0111 1	111 1111	+V _{IN} (2047/2048)					
0000 00	000 0001	+V _{IN} (1/2048)					
0000 00	0000 000	0V					
1111 1	111 1111	-V _{IN} (1/2048)					
1000 00	0000 0000	-V _{IN} (2048/2048)					

TABLE II. Binary Two's Complement Code Table for Circuit of Figure 3.

 R_3 , R_4 , and R_5 must match within 0.01% and must be the same type of resistors (preferably wire-wound or metal foil), so that the temperature coefficients match; mismatch of R_3 value to R_4 causes both offset and full-scale error. Mismatch of R_5 to R_4 and R_3 causes full-scale error.



FIGURE 3. Bipolar Operation (binary two's complement code).



DIGITALLY-CONTROLLED GAIN BLOCK

Figure 4 shows a circuit for a digitally-controlled gain block. The feedback for the op amp is made up of the FET switch and the R-2R ladder. The input resistor to the gain block is the R_{FB} of the DAC7545. As the FET switch is in the feedback loop, a zero code into the DAC will result in the op amp having no feedback, and a saturated op amp output.



FIGURE 4. Digitally Controlled Gain Block.

APPLICATION HINTS

CMOS DACs, such as the DAC7545, exhibit a code-dependent out resistance. The effect of this is a code-dependent differential nonlinearity at the amplifier output that depends on the offset voltage, V_{OS} , of the amplifier. Thus linearity depends upon the potential of OUT 1 and AGND being exactly equal to each other. Usually the DAC is connected to an external op amp with the noninverting input connected to AGND. The op amp selected should have a low input bias current and low V_{OS} and V_{OS} drift over temperature. The op amp offset voltage should be less than $(25 \cdot 10^{-6})(V_{REF})$ over operating conditions. Suitable op amps are the OPA37 and the OPA627 for fixed

reference applications and low-bandwidth requirement; the OPA37 has low V_{OS} and does not require an offset trim. For wide bandwidth, high slew rate, or fast-settling applications, the OPA604 or 1/2 OPA2604 are recommended.

Unused digital inputs must be connected to V_{DD} or to DGND, this prevents noise from triggering the high impedance digital input. It is suggested that the unused digital inputs also be given a path to ground or V_{DD} through a 1mW resistor to prevent the accumulation of static charge if the PC card is unplugged from the system. In addition, in systems where the AGND to DGND connection is on a backplane, it is recommended that two diodes be connected in inverse parallel between AGND and DGND.

INTERFACING TO MICROPROCESSORS

The DAC7545 can be directly interfaced to either an 8- or 16bit microprocessor through its 12-bit wide data latch using the $\overline{\text{CS}}$ and $\overline{\text{WR}}$ controls.

An 8-bit processor interface is shown in Figure 5. It uses two memory addresses: one for the lower 8 bits and one for the upper 4 bits of data into the DAC via the latch.



FIGURE 5. 8-Bit Processor Interface.





13-Jan-2017

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
DAC7545GLP	OBSOLETE	ZZ (BB)	ZZ222	20		TBD	Call TI	Call TI	-40 to 85		
DAC7545GLU	OBSOLETE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 85	DAC7545GLU	
DAC7545GLUG4	OBSOLETE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 85	DAC7545GLU	
DAC7545JP	OBSOLETE	ZZ (BB)	ZZ222	20		TBD	Call TI	Call TI	-40 to 85		
DAC7545JU	OBSOLETE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 85	DAC7545JU	
DAC7545KP	OBSOLETE	ZZ (BB)	ZZ222	20		TBD	Call TI	Call TI	-40 to 85		
DAC7545KU	OBSOLETE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 85	DAC7545KU	
DAC7545KUG4	OBSOLETE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 85	DAC7545KU	
DAC7545LP	OBSOLETE	ZZ (BB)	ZZ222	20		TBD	Call TI	Call TI	-40 to 85		

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



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PACKAGE OPTION ADDENDUM

13-Jan-2017

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



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EXAMPLE BOARD LAYOUT

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



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EXAMPLE STENCIL DESIGN

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







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